

**8550S****PNP SILICON TRANSISTOR****LOW VOLTAGE HIGH
CURRENT SMALL SIGNAL
PNP TRANSISTOR**■ **DESCRIPTION**

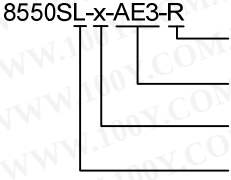
The UTC **8550S** is a low voltage high current small signal PNP transistor, designed for Class B push-pull audio amplifier and general purpose applications.

■ **FEATURES**

- *Collector current up to 700mA
- *Collector-Emitter voltage up to 20 V
- *Complimentary to 8050S

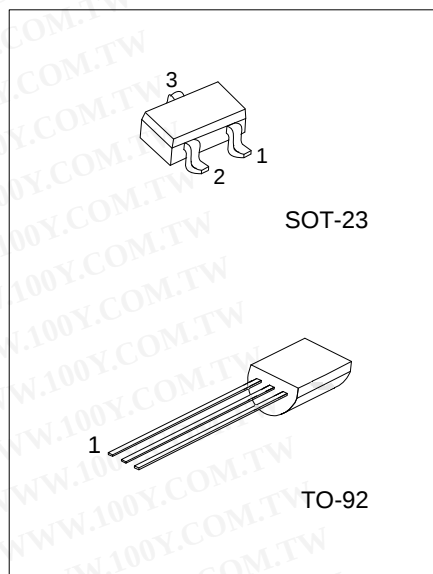
■ **ORDERING INFORMATION**

Ordering Number			Package	Pin Assignment			Packing
Normal	Lead Free	Halogen-Free		1	2	3	
8550S-x-AE3-R	8550SL-x-AE3-R	8550SG-x-AE3-R	SOT-23	E	B	C	Tape Reel
8550S-x-T92-B	8550SL-x-T92-B	8550SG-x-T92-B	TO-92	E	C	B	Tape Box
8550S-x-T92-K	8550SL-x-T92-K	8550SG-x-T92-K	TO-92	E	C	B	Bulk

	(1)Packing Type	(1) B: Tape Box, K: Bulk, R: Tape Reel
	(2)Package Type	(2) AE3: SOT-23, T92: TO-92
	(3)Rank	(3) x: refer to Classification of h_{FE2}
	(4)Lead Free	(4) G: Halogen Free, L: Lead Free, Blank: Pb/Sn

■ **MARKING (For SOT-23 Package)**

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-34970699
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)



■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATING	UNITS
Collector-Base Voltage		V_{CB0}	-30	V
Collector-Emitter Voltage		V_{CEO}	-20	V
Emitter-Base Voltage		V_{EBO}	-5	V
Collector Current		I_C	-700	mA
Collector Dissipation(Ta=25°C)	SOT-23	P_C	350	mW
	TO-92		1	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-40 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta= 25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV_{CB0}	$I_C = -100\mu A, I_E = 0$	-30			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = -1mA, I_B = 0$	-20			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = -100\mu A, I_C = 0$	-5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -30V, I_E = 0$			-1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-100	nA
DC Current Gain	h_{FE1}	$V_{CE} = -1V, I_C = -1mA$	100			
	h_{FE2}	$V_{CE} = -1V, I_C = -150mA$	120		400	
	h_{FE3}	$V_{CE} = -1V, I_C = -500mA$	40			
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	$I_C = -500mA, I_B = -50mA$			-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	$I_C = -500mA, I_B = -50mA$			-1.2	V
Base-Emitter Saturation Voltage	V_{BE}	$V_{CE} = -1V, I_C = -10mA$			-1.0	V
Current Gain Bandwidth Product	f_T	$V_{CE} = -10V, I_C = -50mA$	100			MHz
Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		9.0		pF

■ CLASSIFICATION OF h_{FE2}

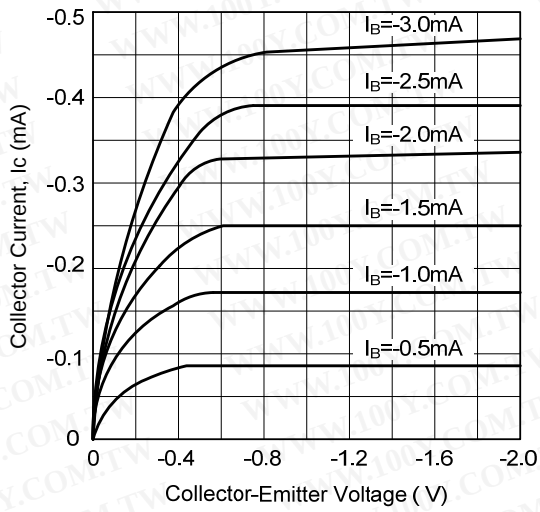
RANK	C	D	E
RANGE	120-200	160-300	280-400

8550S

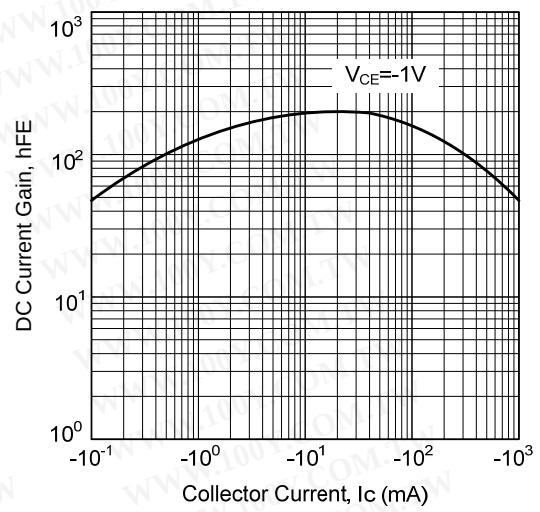
PNP SILICON TRANSISTOR

■ TYPICAL CHARACTERISTICS

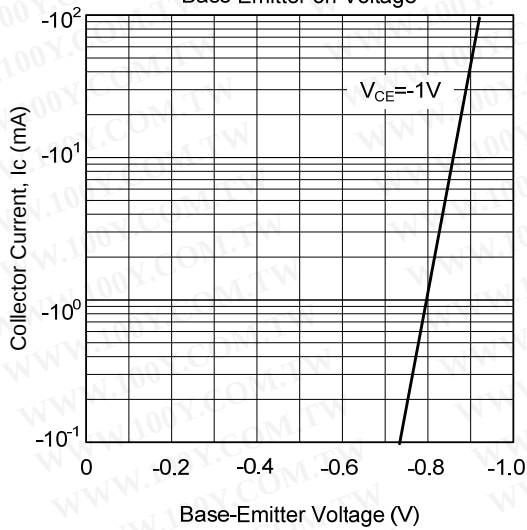
Static Characteristics



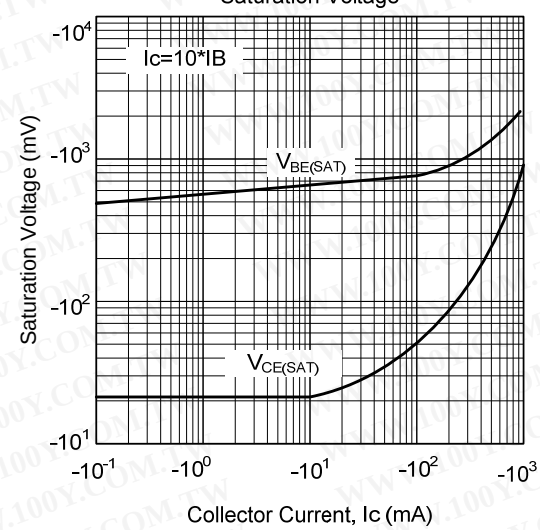
DC Current Gain



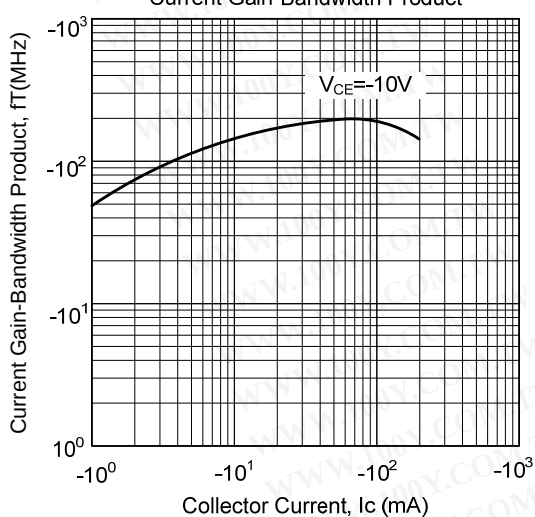
Base-Emitter on Voltage



Saturation Voltage



Current Gain-Bandwidth Product



Collector Output Capacitance

